

**REMARKS**

The Office Action mailed November 6, 2002, has been carefully reviewed. In a Response to Restriction Requirement dated September 9, 2002, Applicants elected claims 1-6 and 11-17 for examination. By this amendment, Applicants have amended claims 1, 2, 4-6 and 14-17 for the purpose of clarifying and correcting minor grammatical issues. The claim amendments are not intended to narrow Applicants' claimed invention in any manner. No new matter has been added. Entry of this amendment is therefore respectfully requested. Accordingly, claims 1-6 and 11-17 are pending and are submitted for consideration by the Examiner.

**Summary of the Office Action**

Figure 1 stands objected to for failing to include a legend such as "Prior Art." Claims 5 and 6 stand objected to because of informalities. Claims 1 and 2 stand rejected under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter. Claims 1, 2, and 3 stand rejected under 35 U.S.C. § 102(e) as being anticipated by *Sun et al.* (U.S. Patent No. 6,058,124). Claims 4-6, and 11-17 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over *Sun et al.* in view of *Nakata* (U.S. Patent No. 4,152,711), and *Bour et al.* (U.S. Patent No. 6,233,265).

**The Objection to the Drawings**

The Office Action states that Figure 1 should be designated by a legend such as "Prior Art" because only that which is old is illustrated. In a Request for Approval of Drawing Change submitted herewith, Applicants have submitted a new sheet proposing that the legend "PRIOR

ART" be added to Figure 1 in accordance with the Examiner's suggestion. Accordingly, approval of the proposed drawing change and withdrawal of the objection to the drawing is respectfully requested.

### **The Objection to Claims 5 and 6**

In the Office Action, the use of the term "any" in claims 5 and 6 is objected to. It is believed that this objection has been obviated by the amendments to the claims. Accordingly, Applicants respectfully request withdrawal of this objection.

### **The Rejection Under 35 U.S.C. 112, Second Paragraph**

Claims 1 and 2 stand rejected under 35 U.S.C. § 112, second paragraph, as allegedly being indefinite for failing to particularly point out and distinctly claim the invention. The connectivity between p-side and n-side electrodes of the first and second laser units has been clarified by the amendments to the claims. In particular, the p-side electrode of the first laser unit is electrically connected to the n-side electrode of the second laser unit and the n-side electrode of the first laser unit is electrically connected to the p-side electrode of the second laser unit, as recited in amended claim 1. Accordingly, withdrawal of all rejections under 35 U.S.C. § 112, second paragraph, is respectfully requested.

### **The Rejection Under 35 U.S.C. 102(e)**

Claims 1, 2, and 3 stand rejected under 35 U.S.C. § 102(e) as being anticipated by *Sun et al.* (U.S. Patent No. 6,058,124).

Regarding the rejection of claims 1, 2, and 3 under 35 U.S.C. § 102(e) as allegedly being anticipated by *Sun et al.*, it is asserted in the Office Action that Fig. 2 of *Sun et al.* depicts the claimed connectivity between p-side and n-side electrodes of the first and second laser units. However, Applicants respectfully submit that this is not correct because, although the IR laser 120 and the red laser 140 of *Sun et al.* appear to share a common n-type substrate, there is no connectivity depicted between the p-side electrode of the first laser unit and the n-side electrode of the second laser unit, or the n-side electrode of the first laser unit and the p-side electrode of the second laser unit, as claimed. In fact, in contrast to the claimed invention, as correctly recognized by the Examiner the IR laser 120 and the red laser 140 are isolated from each other by the isolation groove 224. Accordingly, *Sun et al.* fails to anticipate or render obvious the claimed invention, at least because *Sun et al.* fails to teach or suggest the claimed connectivity between p-side and n-side electrodes of the first and second laser units. For these reasons, withdrawal of the rejection under 35 U.S.C. § 102(e) of claims 1, 2, and 3 is respectfully requested.

### **The Rejection Under 35 U.S.C. 103(a)**

Claims 4-6, and 11-17 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over *Sun et al.* in view of *Nakata*, and *Bour et al.*.

Regarding the rejection of dependent claims 4-6, and 11-17 under 35 U.S.C. § 103(a) as allegedly being unpatentable over *Sun et al.* in view of *Nakata* and *Bour et al.*, these claims are allowable at least because they further limit allowable base claims. Accordingly, withdrawal of the rejection under 35 U.S.C. § 103(a) is respectfully requested.

Attached hereto is a marked-up version of the changes made to the claims by the current Amendment. The attached page is captioned "**VERSIONS WITH MARKINGS TO SHOW CHANGES MADE.**"

**CONCLUSION**

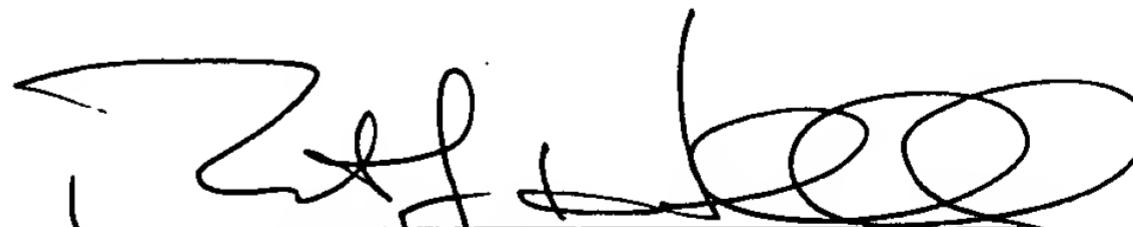
In view of the foregoing, Applicants respectfully request reconsideration and the timely allowance of the pending claims. Should the Examiner feel that there are any issues outstanding after consideration of this response, the Examiner is invited to contact Applicants' undersigned representative to expedite prosecution.

**EXCEPT** for issue fees payable under 37 C.F.R. § 1.18, the Commissioner is hereby authorized by this paper to charge any additional fees during the entire pendency of this application including fees due under 37 C.F.R. §§ 1.16 and 1.17 which may be required, including any required extension of time fees, or credit any overpayment to Deposit Account 50-0310. This paragraph is intended to be a **CONSTRUCTIVE PETITION FOR EXTENSION OF TIME** in accordance with 37 C.F.R. § 1.136(a)(3).

Respectfully submitted,

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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE CLAIMS:**

Claims 1, 2, 4-6, and 14-17 have been amended as follow:

1. (Amended) A semiconductor laser device including first and second laser units, each unit having a ridge type structure and each unit comprising a multilayer structure body made of at least an n-type semiconductor layer, an active layer and a p-type semiconductor layer deposited in this order, and a p-side electrode and an n-side electrode, wherein the p-side electrode of the first laser unit is electrically connected to the n-side electrode of the second laser unit and the n-side electrode of the first laser unit is electrically connected to [and the n-side electrode and] the p-side electrode of the second laser unit [~~are electrically connected, respectively~~].
  
2. (Amended) The semiconductor laser device according to claim 1, further comprising:  
  
a first connecting layer interconnecting said p-side electrode of the first laser unit and said n-side electrode of the second laser unit; and  
  
a second connecting layer interconnecting between said p-side electrode of the second laser unit and said n-side electrode of the first laser unit [~~wherein the p-side electrode and the n-side electrode of the first laser unit and the n-side electrode and the p-side electrode of the second laser unit are electrically connected, respectively through respective connecting layers~~].

4. (Twice Amended) The semiconductor laser device according to claim 2, wherein at least one of said first and said second connecting layers [the connecting layers] has a Schottky barrier.

5. (Twice Amended) The semiconductor laser device according to claim [any of claims] 1, wherein at least one of the first and second laser units has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

6. (Twice Amended) The [A] semiconductor laser device according to claim [any of claims] 1, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

14. (Amended) The [A] semiconductor laser device according to claim 2, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

15. (Amended) The [A] semiconductor laser device according to claim 3, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

16. (Amended) The [A] semiconductor laser device according to claim 4, wherein at least one of the first and second laser units is a semiconductor laser having a gallium (GaN) system semiconductor deposited.

17. (Amended) The [A] semiconductor laser device according to claim 5, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.



1 / 7

PRIOR ART  
FIG. 1

